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(54) **CYLINDRICAL BONDING STRUCTURE AND METHOD OF MANUFACTURE**

(52) **U.S. Cl. 257/737; 257/738; 257/778; 438/108; 438/613; 438/614; 438/615**

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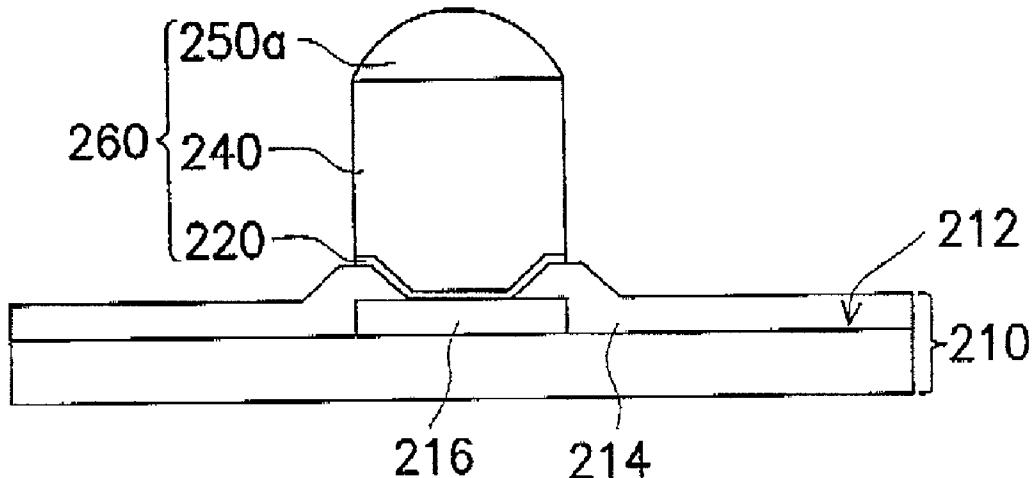
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(57)

ABSTRACT

A cylindrical bonding structure and its method of manufacture. The cylindrical bonding structure is formed over the bonding pad of a silicon chip and the chip is flipped over to connect with a substrate board in the process of forming a flip-chip package. The cylindrical bonding structure mainly includes a conductive cylinder and a solder block. The conductive cylinder is formed over the bonding pad of the silicon chip and the solder block is attached to the upper end of the conductive cylinder. The solder block has a melting point lower than the conductive cylinder. The solder block can be configured into a cylindrical, spherical or hemispherical shape. To fabricate the cylindrical bonding structure, a patterned mask layer having a plurality of openings that correspond in position to the bonding pads on the wafer is formed over a silicon wafer. Conductive material is deposited into the openings to form conductive cylinders and finally a solder block is attached to the end of each conductive cylinder.



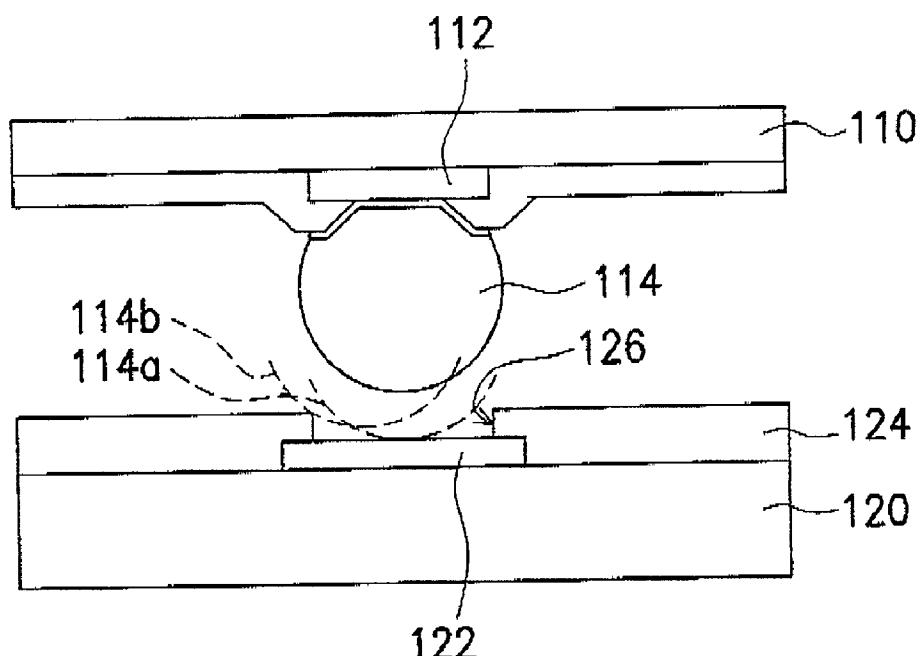


FIG. 1A(PRIOR ART)

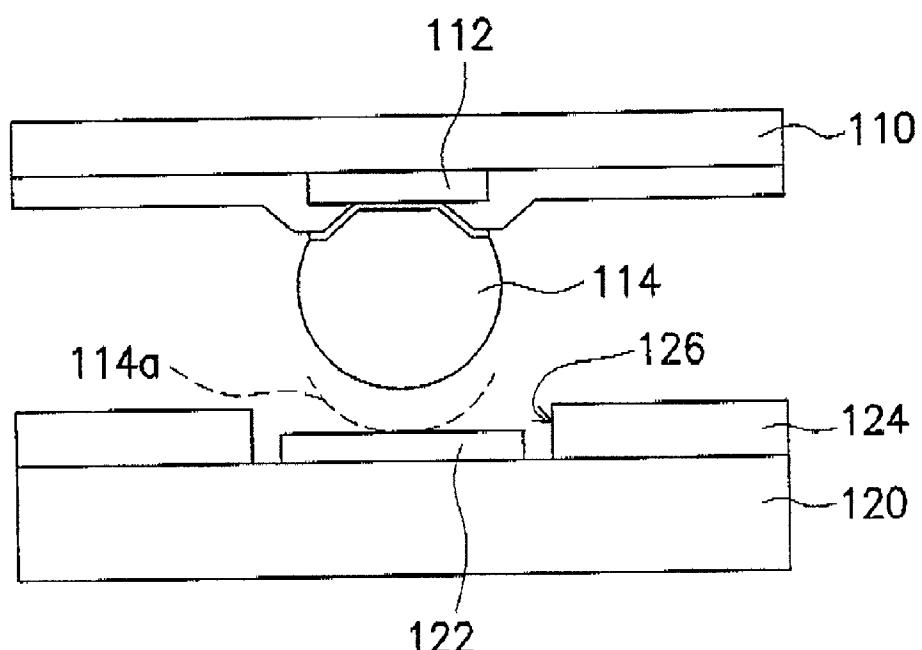


FIG. 1B(PRIOR ART)

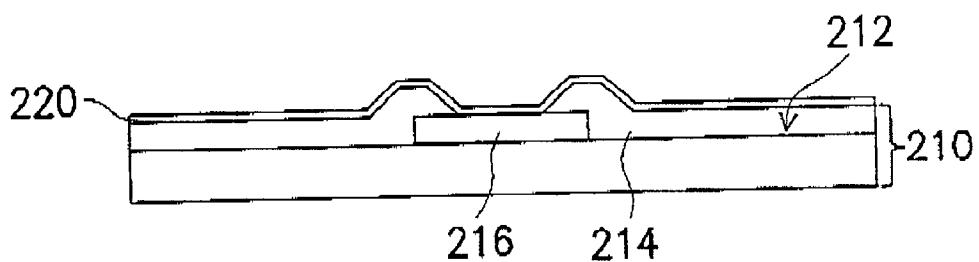


FIG. 2A

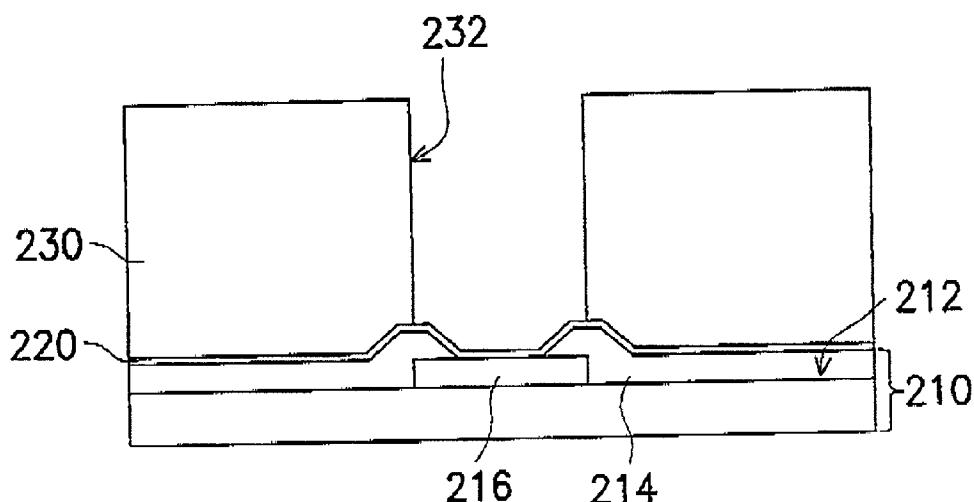


FIG. 2B

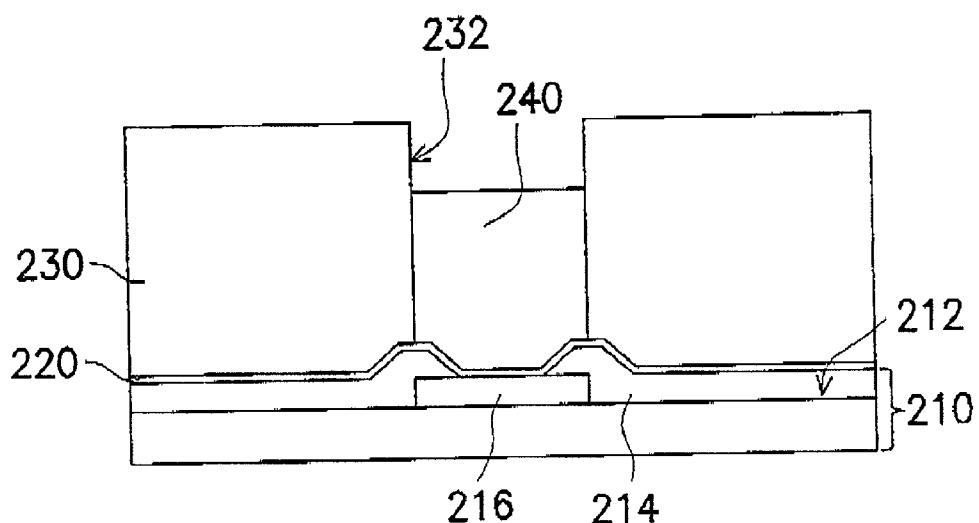


FIG. 2C

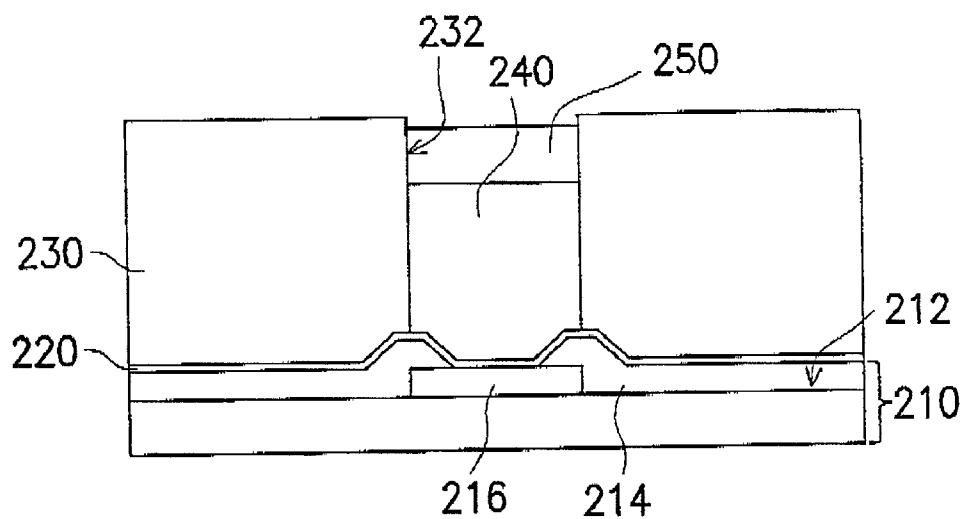


FIG. 2D

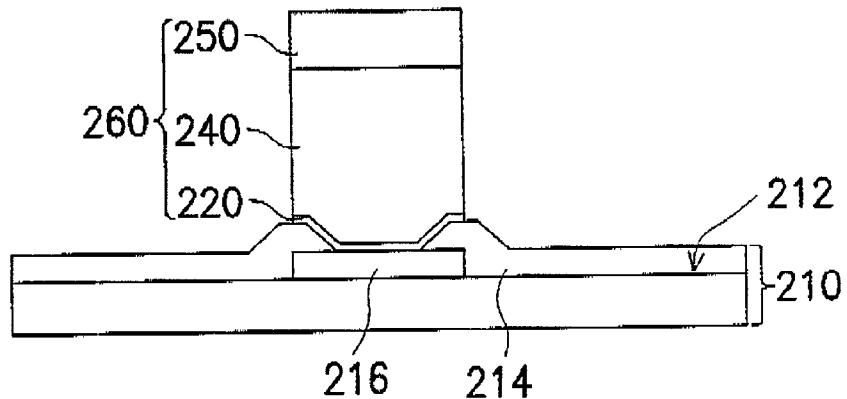


FIG. 2E

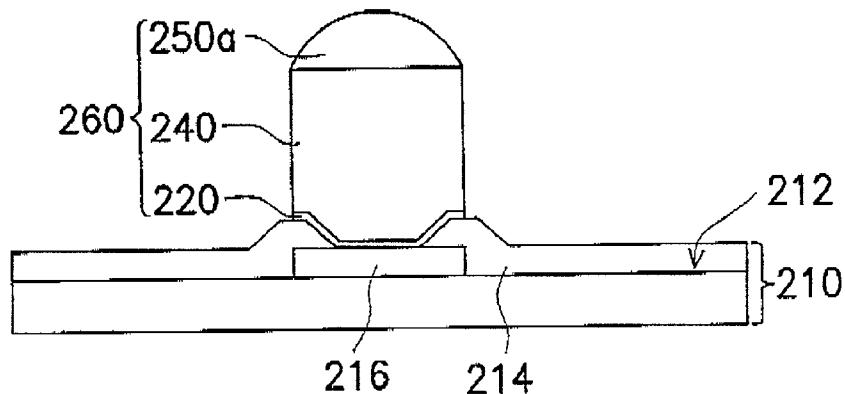


FIG. 2F

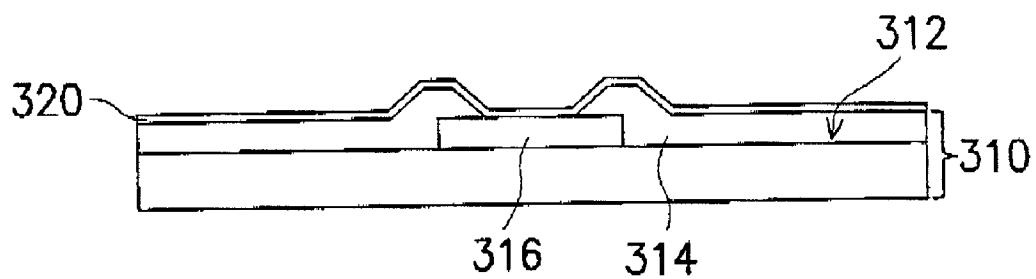


FIG. 3A

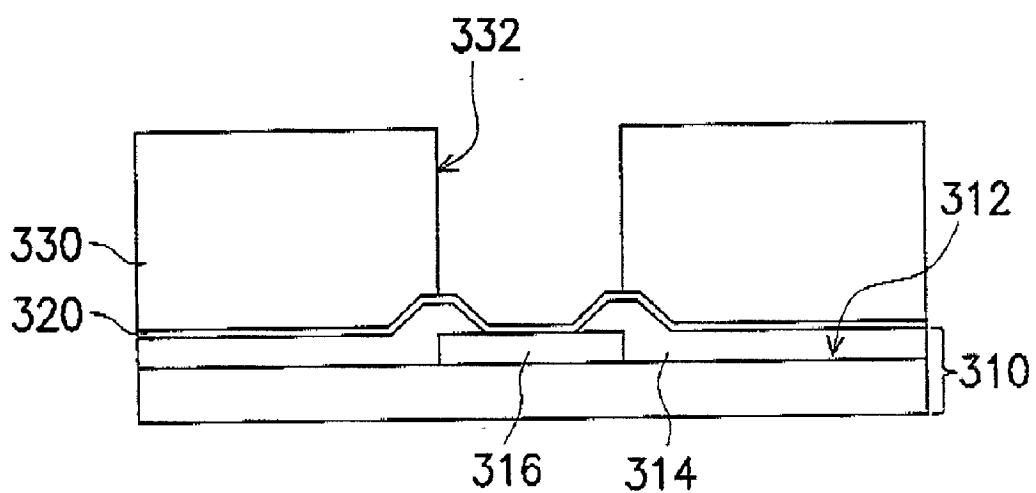


FIG. 3B

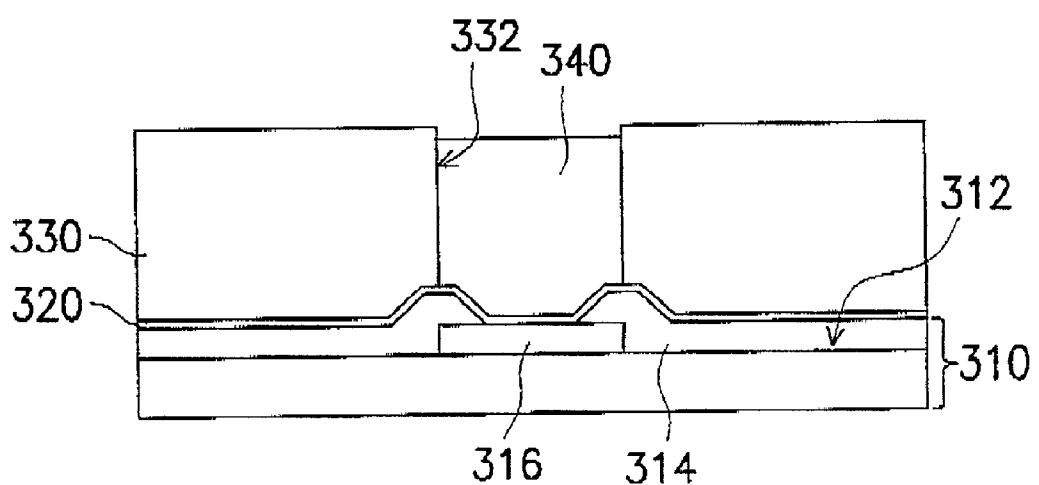


FIG. 3C

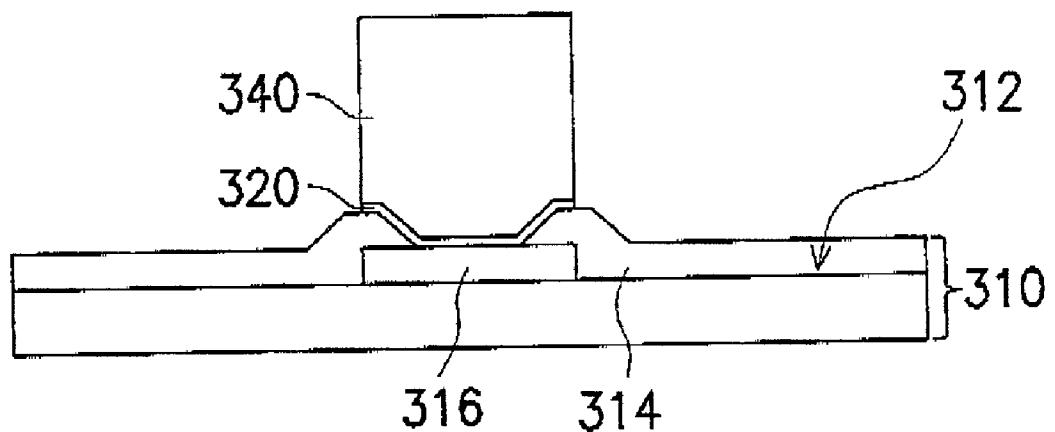


FIG. 3D

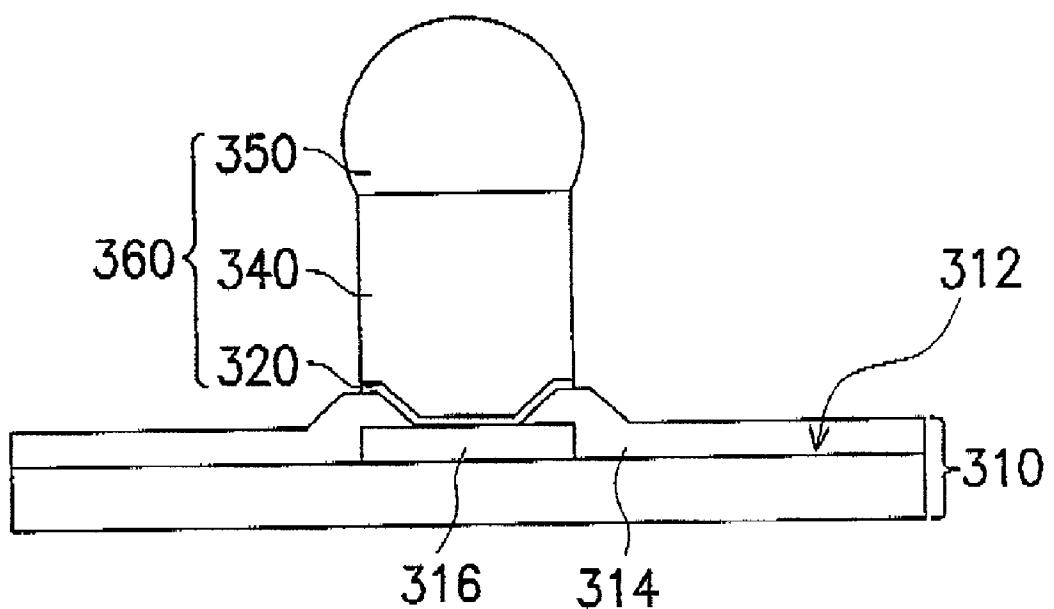


FIG. 3E

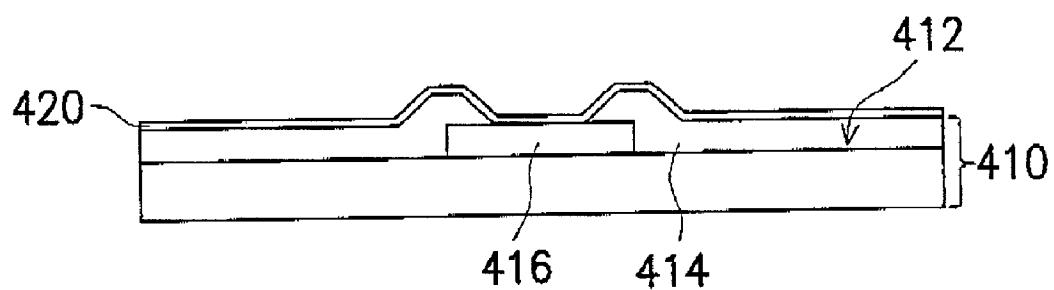


FIG. 4A

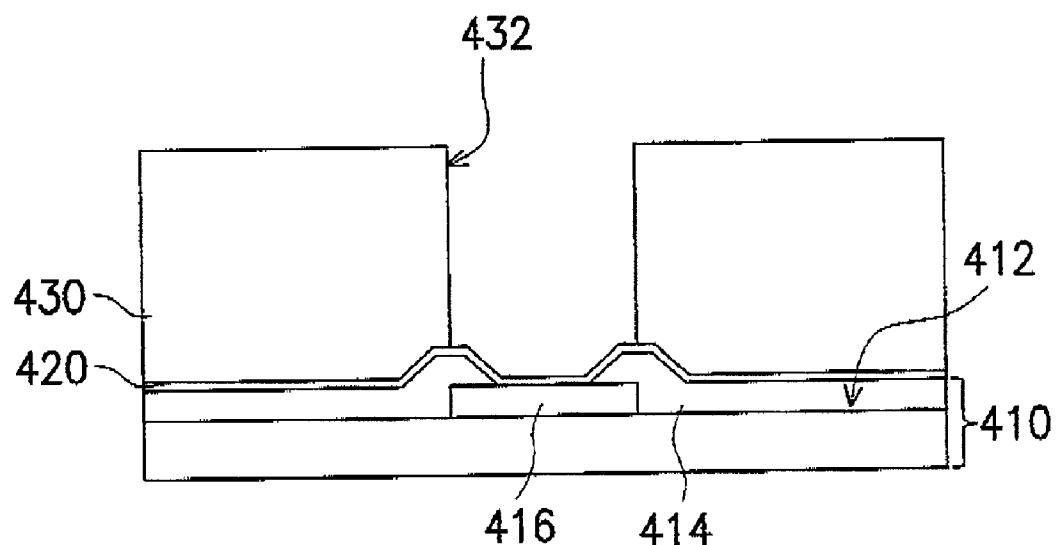


FIG. 4B

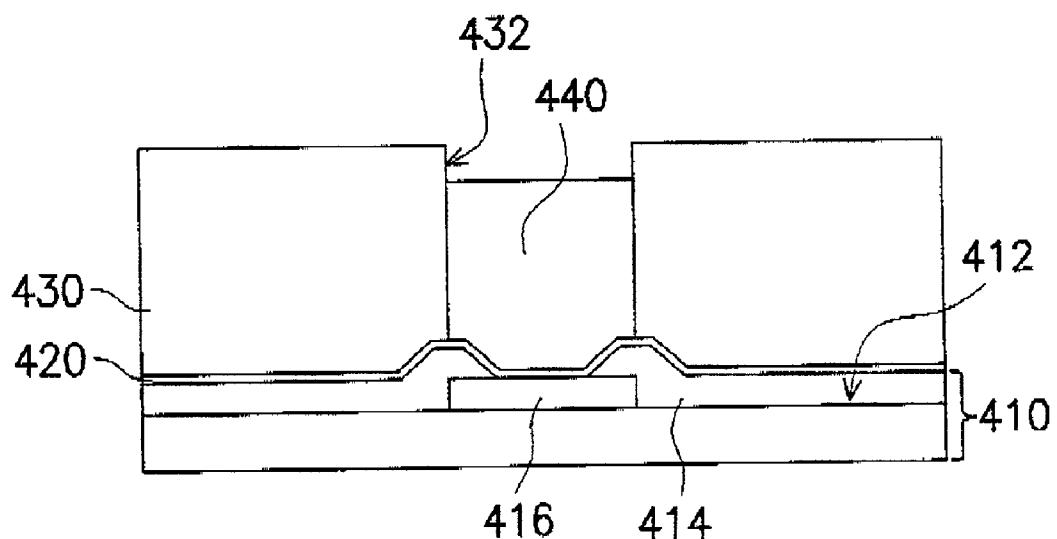
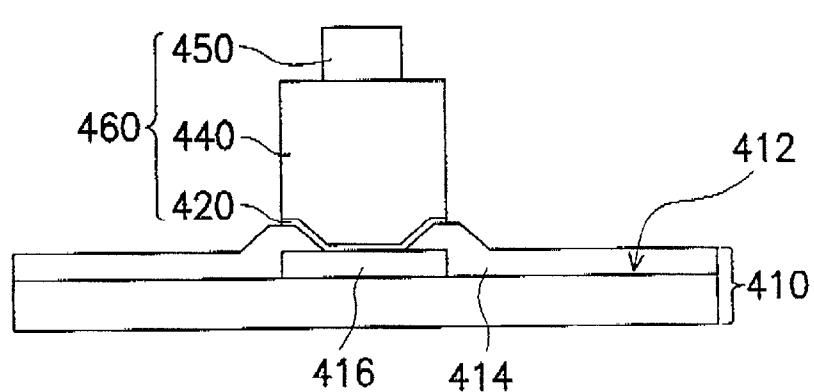
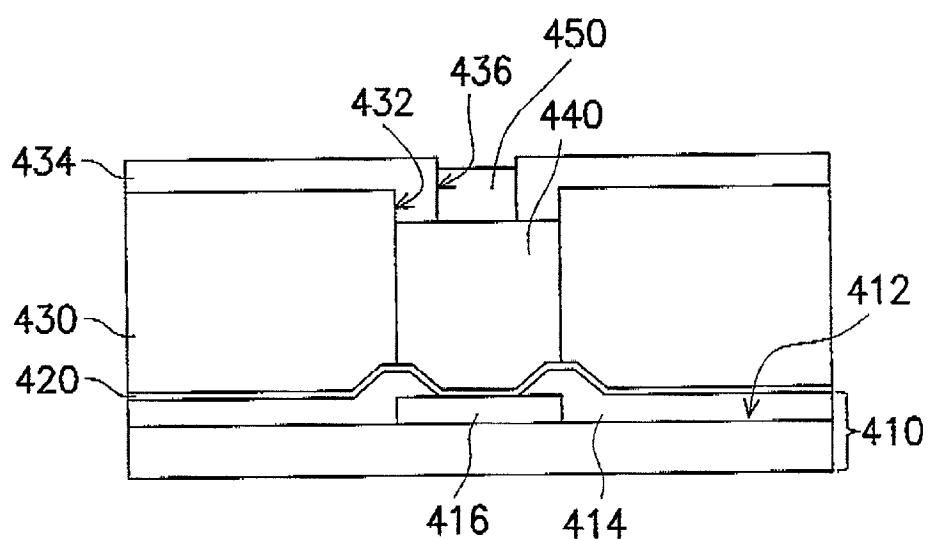
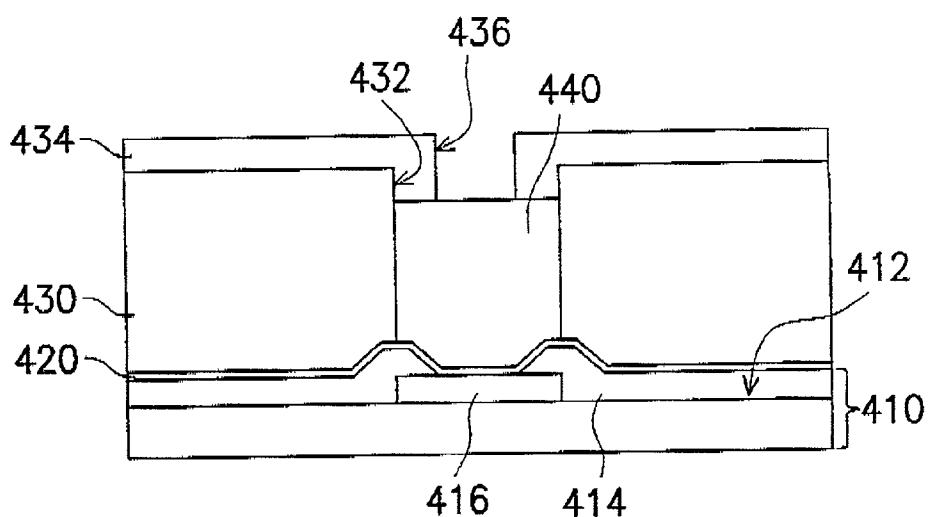


FIG. 4C



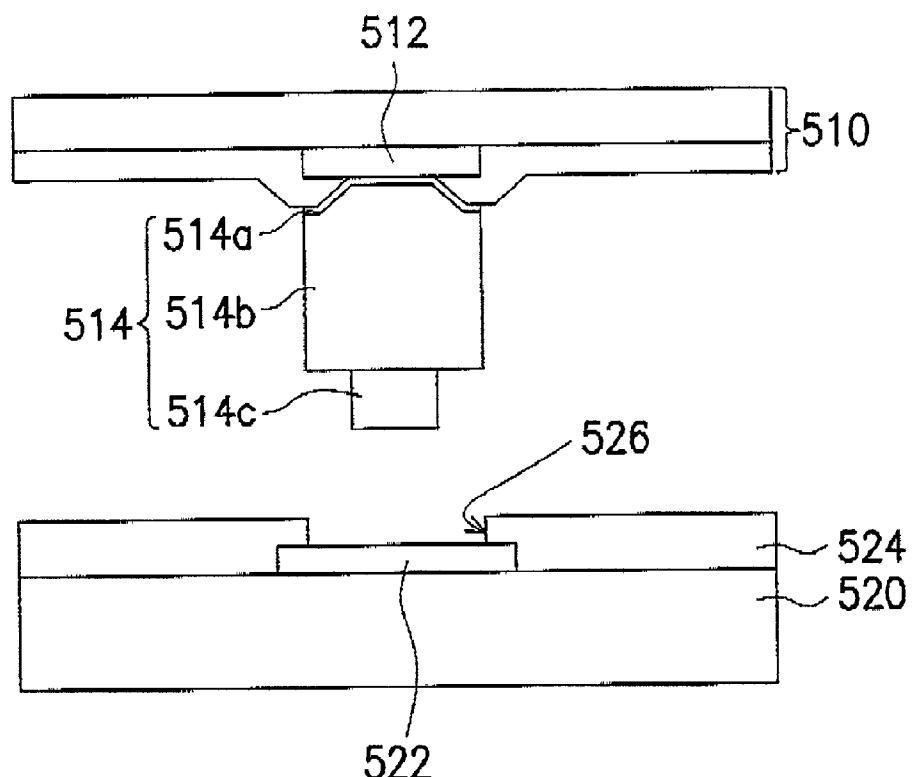


FIG. 5A

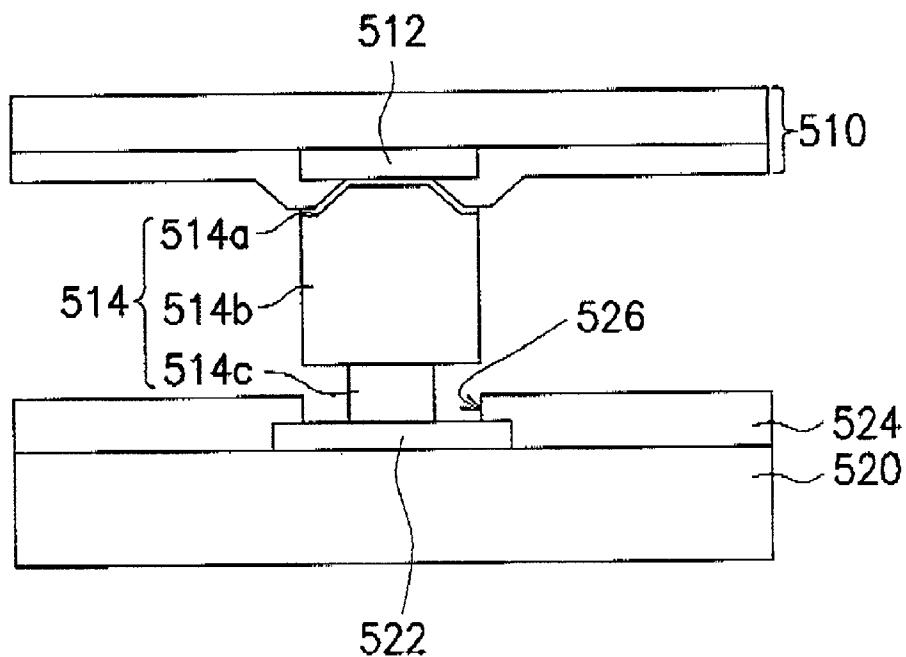


FIG. 5B

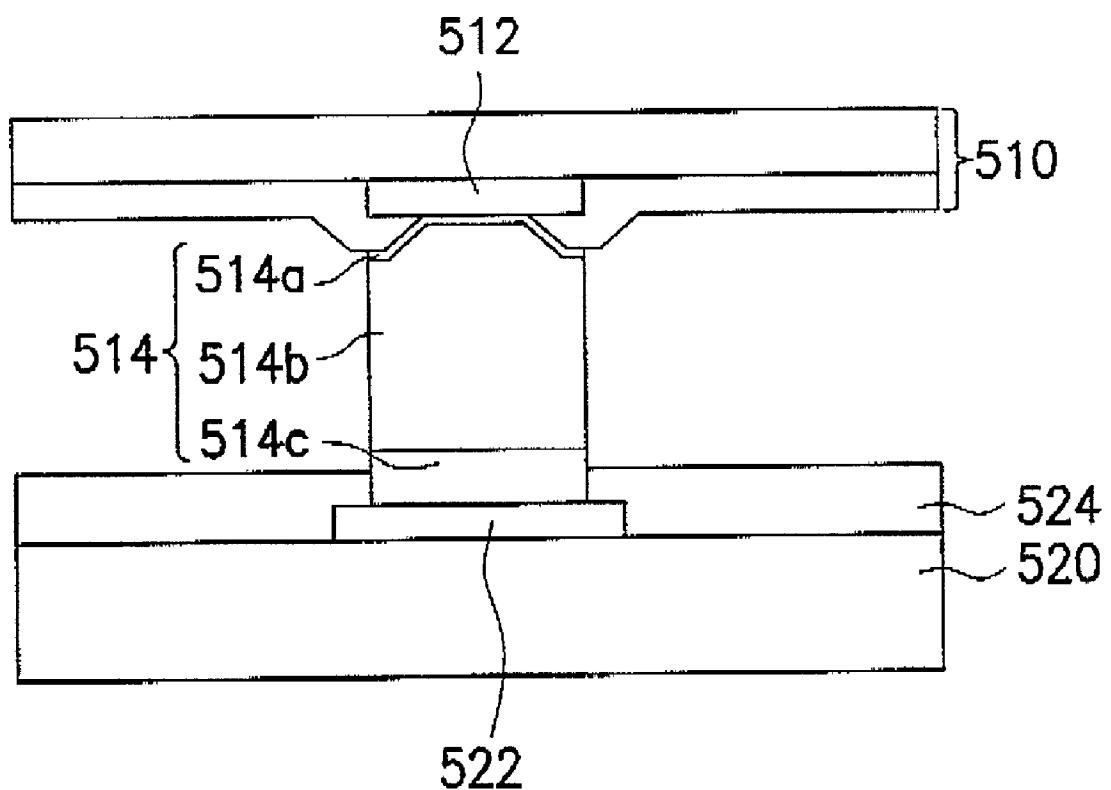


FIG. 5C

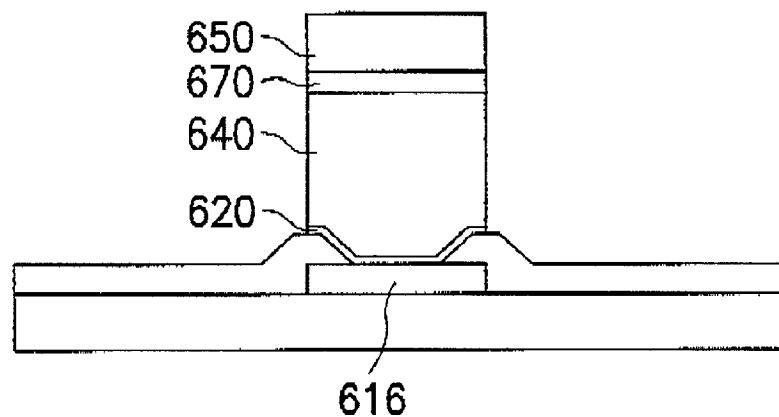


FIG. 6A

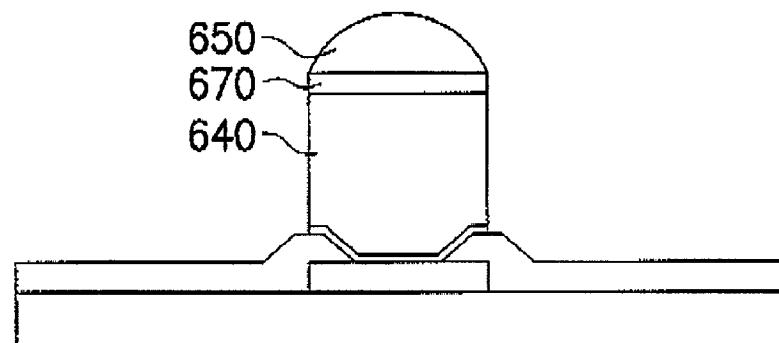


FIG. 6B

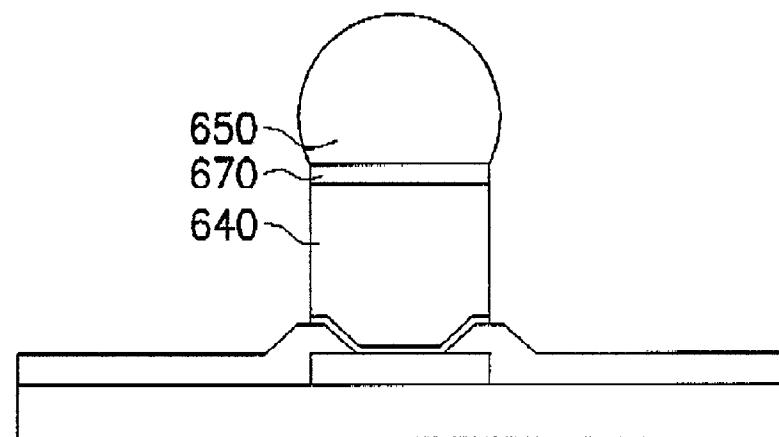


FIG. 6C

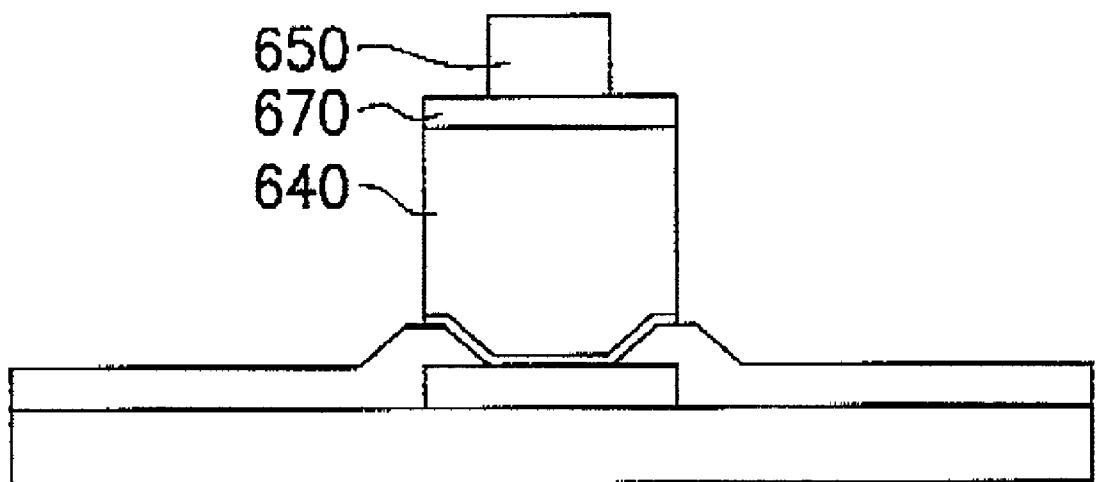


FIG. 6D

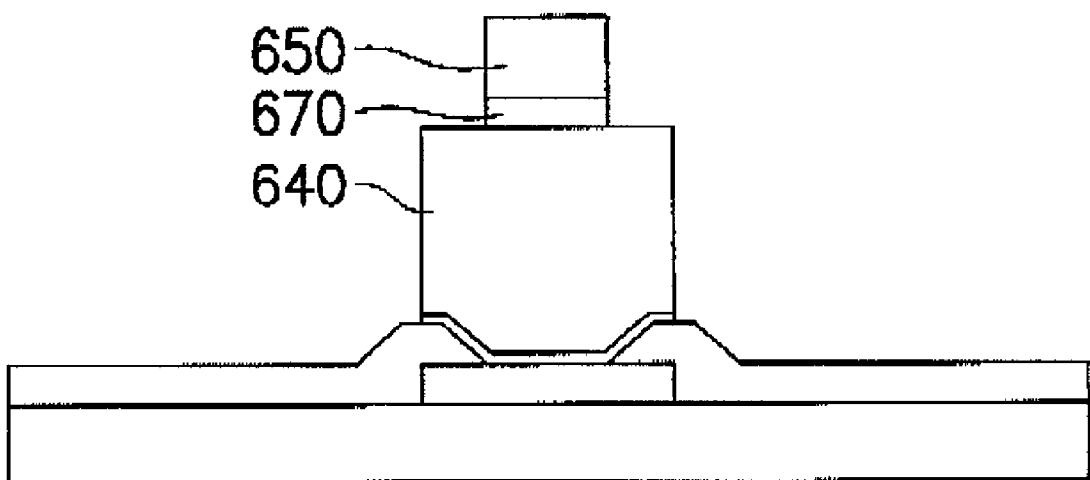


FIG. 6E

CYLINDRICAL BONDING STRUCTURE AND METHOD OF MANUFACTURE

CROSS-REFERENCE TO RELATED APPLICATION

[0001] This application claims the priority benefit of Taiwan application serial no. 91100092, filed Jan. 7, 2002.

BACKGROUND OF THE INVENTION

[0002] 1. Field of Invention

[0003] The present invention relates to a cylindrical bonding structure and its method of manufacture. More particularly, the present invention relates to a cylindrical bonding structure for a flip chip package and a method of fabricating the cylindrical bonding structure.

[0004] 2. Description of Related Art

[0005] In this information-saturated society, working with electronic products has become an integral part of our daily life. Currently, integrated circuit products are used for doing business, educating our children or providing us with games for recreation. As a result of rapid progress in electronic technologies, devices having powerful functions and personalized designs have been developed. Moreover, most electronic products have light and compact design. Nowadays, high-density integrated circuits are frequently housed with in compact semiconductor packages such as a flip-chip package and a ball grid array (BGA) package.

[0006] In the flip-chip technique, bumps are formed on the bonding pads of a chip so that the bumps may be attached to corresponding contact points on a substrate after flip over. Compared with conventional wire bonding and tape automatic bonding (TAB) packaging techniques, a flip-chip package has the shortest signal transmission path between the chip and the substrate and hence has superior electrical properties. In addition, a flip-chip package may be designed to have its back exposed so as to increase heat dissipation rate. Due to the above reasons, flip-chip packaging techniques are widely adopted in the semiconductor fabrication industry.

[0007] FIG. 1A is a partially magnified view showing a connection configuration between a bump on a chip and a contact point on a substrate in a conventional flip-chip package. A chip 110 normally has a plurality of bonding pads 112 (only one is shown in FIG. 1A). Each bonding pad 112 has a bump 114. In general, the bump 114 is a solder bump so that the flip-over chip 110 may directly connect with one of the bonding pads 122 (only one is shown in FIG. 1A) on the substrate 120. Since the chip 110 and the substrate 120 each has a different coefficient of thermal expansion (CTE), a standoff distance must be provided between the chip 110 and the substrate 120 so that differential thermal expansion will not accumulate too much shear stress to break the bumps 114 prematurely.

[0008] Thus, to prevent shear stress from damaging the bumps 114, bumps 114 having a great height are often attached to the bonding pads 112 of the chip 110 so as to increase the distance of separation between the chip 110 and the substrate 120 as much as possible. However, increasing the overall height of the bumps 114 must be accompanied by a corresponding increase in outer diameter and volume of

the bumps. Moreover, to prevent short-circuiting, pitch between neighboring bumps 114 must be increased. Ultimately, distance between neighboring bonding pads 112 on the chip 110 is hard to reduce.

[0009] In addition, pre-solder material is often applied on the junction pads 122 of the substrate 120 before the lower end of the bumps 114 are put against the pads 122. In a reflow operation, the low melting point pre-solder melts and joins the bumps 114 and the junction pads 122 together. Because an additional step of applying low melting point solder over the junction pads 122 of the substrate 120 has to be conducted, cost of fabricating the substrate 120 is increased. Furthermore, to increase the distance of separation between the chip 110 and the substrate 120, high lead solder is a principle ingredient of the bumps 114. Since a high temperature treatment of the bump material to form a spherical shape bump often produces oxide material near the surface, the bumps 114 and the junction pads 122 often have poor adhesion after the solder reflow process. Poor adhesion often leads to bad electrical connections between the chip and the substrate and a low overall yield of the flip chip package.

[0010] FIG. 1B is a partially magnified view showing an alternative connective configuration between a bump on a chip and a contact point on a substrate in a conventional flip-chip package. A solder mask 124 is formed over the substrate 120 to pattern out contact area around the junction pads 122. In fact, there are two major patterning techniques that employ the solder mask 124. The first one is called a 'solder mask define' (SMD) and the other one is called a 'no solder mask define' (NSMD). In FIG. 1A, a 'solder mask define' (SMD) technique is used. An opening 126 in the solder mask 124 exposes a portion of the junction pad 122 so that a bump on the chip 110 is in a corresponding position over the junction pad 122 on the substrate 120. In FIG. 1B, a 'no solder mask define' (NSMD) technique is used. An opening 126 in the solder mask 124 completely exposes a junction pad 122 so that a bump is completely connected to the junction pad 122. The most commonly used material for forming the solder mask 124 is, for example, green lacquer.

[0011] To shorten pitch between neighboring junction pads 122, SMD technique such as the one shown in FIG. 1A is often employed. Only a portion of the junction pad 122 is exposed through the solder mask 124 for contact with the lower edge of a bump 114 (shown in profile by dash lines 114a). However, because actual dimension of a bump 114 may vary from the standard dimension by $\pm 10\%$, variation in positional accuracy between the bump 114 and the junction pad 122 of up to $10\mu\text{m}$ is possible. Furthermore, the opening 126 in the solder mask layer 124 may have an intrinsic diametrical variation of about $15\mu\text{m}$. Hence, when the bump 114 and the junction pad 122 are laid on top of each other, the lower edge of the bump 114 may not come into direct contact with the surface of the junction pad 122. In extreme cases, part of the outer edge of the bump 114 may lean upon the upper corner of the opening 126 of the solder mask layer 124 shown by the dash line 114b in FIG. 1A. Hence, after a solder reflow operation, the bump 114 may not be properly bonded with the junction pad 122 to form a good electrical connection. To ensure proper bonding between the lower edge of the bump 114 with the junction pad 122, diameter of the opening 126 of a conventional solder mask 124 is generally larger than the external diam-

eter of the bump 114. Since distance between neighboring junction pads 122 must be increased to accommodate the extension, ultimate level of integration is greatly reduced.

SUMMARY OF THE INVENTION

[0012] Accordingly, one object of the present invention is to provide a cylindrical bonding structure and its method of manufacture capable of reducing the separation between neighboring bonding pads on a chip while increasing distance of separation between the chip and a substrate. Ultimately, reliability of the junctions connecting the chip and the substrate is improved and post-packaging life of the chip is extended.

[0013] A second object of this invention is to provide a cylindrical bonding structure and its method of manufacture capable of reducing the diameter of openings on a solder mask for exposing a junction pad so that distance of separation between neighboring junction pads on the substrate is reduced. Consequently, the distance of separation between neighboring bonding pads (bumps) on the chip is also reduced.

[0014] A third object of this invention is to provide a cylindrical bonding structure and its method of manufacture that requires no application of low melting point solder material on the junction pads of a substrate or the surface of bumps before conducting a reflow process. Thus, production cost of a flip-chip package is reduced.

[0015] To achieve these and other advantages and in accordance with the purpose of the invention, as embodied and broadly described herein, the invention provides a cylindrical bonding structure and its method of manufacture. A ball contact metallic layer is formed over the entire surface of a silicon wafer. A patterned mask layer is formed over the ball contact metallic layer. The mask layer has openings that correspond in position to bonding pads on the wafer and expose a portion of the underlying ball contact metallic layer. By conducting an electroplating process, for example, conductive material is deposited into the openings of the mask layer to form conductive cylinders. Through electroplating or printing, solder material is deposited into the openings of the mask layer to form a cylindrical solder cap on the upper surface of the conductive cylinders. The mask layer and the ball contact metallic layer outside the conductive cylinder are removed. The residual ball contact metallic layer, the conductive cylinder and the solder cap together form a cylindrical bonding structure. In addition, the cylindrical solder cap may undergo a reflow treatment to transform the cylindrical solder cap into a solder block attached to the upper surface of the conductive cylinder. Alternatively, the deposition of solder material into the openings may be deleted. After the formation of the conductive cylinders, the mask layer and the ball contact metallic layer outside the conductive cylinders are removed. Thereafter, a ball implant process is conducted to attach a solder ball directly onto the exposed surface of each conductive cylinder. The residual ball contact metallic contact, the conductive cylinder and the solder ball together form a cylinder bonding structure.

[0016] This invention also provides an alternative cylindrical bonding structure and its method of manufacture. A ball contact metallic layer is formed over the entire surface of a silicon wafer. A patterned first mask layer is formed over

the ball contact metallic layer. The first mask layer has openings that correspond in position to bonding pads on the wafer and expose a portion of the underlying ball contact metallic layer. By conducting an electroplating process, for example, a conductive material is deposited into the openings of the mask layer to form a conductive cylinder. A patterned second mask layer is formed over the first mask layer. The second mask layer has openings that expose the upper surface of the conductive cylinders. Similarly, by conducting another electroplating operation, solder material is deposited into the openings of the mask layer to form cylindrical solder caps on the upper surface of all conductive cylinders. The first mask layer, the second mask layer, and the ball contact metallic layer outside the conductive cylinder are removed. The residual ball contact metallic layer, the conductive cylinder and the cylindrical solder cap together form a cylindrical bonding structure. In addition, the cylindrical solder cap may be designed to have an outer diameter smaller than the diameter of the opening in the solder mask. Hence, the cylindrical solder cap may pass through the solder mask opening to contact the junction pad on the substrate when the chip is flipped over the substrate.

[0017] It is to be understood that both the foregoing general description and the following detailed description are exemplary, and are intended to provide further explanation of the invention as claimed.

BRIEF DESCRIPTION OF THE DRAWINGS

[0018] The accompanying drawings are included to provide a further understanding of the invention, and are incorporated in and constitute a part of this specification. The drawings illustrate embodiments of the invention and, together with the description, serve to explain the principles of the invention. In the drawings,

[0019] FIG. 1A is a partially magnified view showing a connection configuration between a bump on a chip and a contact point on a substrate in a conventional flip-chip package;

[0020] FIG. 1B is a partially magnified view showing an alternative connective configuration between a bump on a chip and a contact point on a substrate in a conventional flip-chip package;

[0021] FIGS. 2A~2F are schematic cross-sectional views showing the progression of steps for producing a cylindrical bonding structure according to a first embodiment of this invention;

[0022] FIGS. 3A~3E are schematic cross-sectional views showing the progression of steps for producing a cylindrical bonding structure according to a second embodiment of this invention;

[0023] FIGS. 4A~4F are schematic cross-sectional views showing the progression of steps for producing a cylindrical bonding structure according to a third embodiment of this invention;

[0024] FIGS. 5A~5C are schematic cross-sectional views showing an application of the third cylindrical bonding structure according to this invention to the fabrication of a flip-chip package; and

[0025] FIGS. 6A~6E are cross-sectional views showing cylindrical bonding structures fabricated according to this

invention with each cylindrical bonding structure having an addition transition layer between the conductive cylinder and the solder cap.

DESCRIPTION OF THE PREFERRED EMBODIMENTS

[0026] Reference will now be made in detail to the present preferred embodiments of the invention, examples of which are illustrated in the accompanying drawings. Wherever possible, the same reference numbers are used in the drawings and the description to refer to the same or like parts.

[0027] FIGS. 2A~2F are schematic cross-sectional views showing the progression of steps for producing a cylindrical bonding structure according to a first embodiment of this invention. As shown in FIG. 2A, a silicon wafer 210 is provided. Since each chip (not shown) is formed by cutting up the wafer 210 and any redistribution layer or bumps are formed before cutting, the wafer 210 actually represents a congregation of uncut chips. Furthermore, the active surface 212 of the wafer 210 has a passivation layer 214 and a plurality of bonding pads 216 (only one bonding pad is shown in FIG. 2A). The active surface 212 of the wafer 210 refers to the side of the wafer 210 where active devices are formed. The patterned passivation layer 214 exposes the bonding pads 216. Note that bonding pads 216 includes those original pads on the chips or the bonding pads of any redistribution circuit layer on the chips. The purpose of having a redistribution layer is to relocate the original bonding pads on the chip to some other places on the chip.

[0028] As shown in FIG. 2A, a ball contact metallic layer 220 is formed over the entire active surface 212 (that is, the passivation layer 214) of the wafer 210 by conducting, for example, an electroplating operation, an evaporation plating operation or sputtering. The ball contact metallic layer 220 covers the bonding pads 216 and serves as an interface between a subsequently formed conductive cylinder 240 (as shown in FIG. 2C) and the bonding pad 216. Hence, the ball contact metallic layer must be a material that produces as little stress as possible, has a high adhesive strength, resists corrosion and sticks to surface quite easily. In general, the ball contact metallic layer is a composite layer comprising two or more metallic layers, for example, including an adhesive layer and a wetting layer. Common metallic material for fabricating the ball contact metallic layer includes titanium (Ti), tungsten (W), chromium (Cr), copper (Cu), nickel (Ni), cobalt (Co), silver (Ag), gold (Au), tin (Sn), vanadium (V), palladium (Pd) or an alloy of some of the aforementioned metals.

[0029] As shown in FIG. 2B, a patterned mask layer 230 is formed over the ball contact metallic layer 220. The mask layer 230 has a plurality of openings 232 (only one is shown in FIG. 2B) that corresponds in position to the bonding pads 216 and exposes a portion of the ball contact metallic layer 220. The patterned mask layer 230 is formed, for example, by forming a photoresist layer over the ball contact metallic layer 220, conducting a photographic exposure and developing the photoresist layer. Aside from depositing photoresist and conducting photographic procedures, the mask layer 230 with openings 232 thereon may also be formed by a corresponding method using some other materials.

[0030] As shown in FIG. 2C, an electroplating operation is conducted to deposit conductive material into the opening

232 using the ball contact metallic layer 220 as a seed layer. The opening 232 is partially filled to form a conductive cylinder 240 over the ball contact metallic layer 220. The conductive material deposited into the opening 232 is a high melting point metal or alloy such as tin (Sn), lead (Pb), copper (Cu), gold (Au), silver (Ag), zinc (Zn), bismuth (Bi), magnesium (Mg), antimony (Sb), indium (In) or an alloy containing various combination of the aforementioned metals.

[0031] As shown in FIG. 2D, an electroplating operation or a printing operation is conducted to fill the remaining space of the opening 232 with solder material using the conductive cylinder 240 as a seed layer. The solder material forms a cylindrical solder cap 250 over upper surface of the conductive cylinder 240. Note that the solder material is a metal or alloy having a melting point lower than that of the conductive cylinder. Suitable solder material includes tin (Sn), lead (Pb), copper (Cu) gold (Au), zinc (Zn), bismuth (Bi), magnesium (Mg), antimony (Sb), indium (In) or an alloy containing various combinations of the aforementioned metals.

[0032] As shown in FIG. 2E, the mask layer 230 and the ball contact metallic layer 220 outside the conductive cylinder 240 are removed. The reserved ball contact metallic layer 220, the conductive cylinder 240 and the cylindrical solder cap together constitute a cylindrical bonding structure 260. As an example, the conductive cylinder 240 may contain tin and lead in the ratio 5:95 (5Sn/95Pb) or 10:90 (10Sn/90Pb) and the cylindrical solder cap 250 may contain tin and lead in the ratio 63:37 (63Sn/37Pb) or 60:40 (60Sn/40Pb). The conductive cylinder 240 can also be a copper rod while the cylindrical solder cap 250 can be a tin cap. Alternatively, the conductive cylinder 240 can be a rod made from a high melting point lead-free alloy such as a tin-silver-copper (Sn/Ag/Cu) alloy and the cylindrical solder cap 250 can be a cap made from a low melting point lead-free alloy such as tin-bismuth (Sn/Bi) alloy.

[0033] As shown in FIG. 2F, a reflow treatment is conducted after the cylindrical bonding structure 260 is exposed. In the reflow process, the cylindrical solder cap 250 is partially melted to form a solder block 250a having a hemispherical profile over the upper surface of the conductive cylinder 240.

[0034] As shown in FIGS. 2E and 2F, the cylindrical bonding structure 260 of the first embodiment mainly comprises the conductive cylinder 240 and the solder block 250a. The solder block may have a cylindrical shape (the cylindrical solder cap 250 shown in FIG. 2E) or a hemispherical shape (shown in FIG. 2F). The cylindrical bonding structure 260 serves a similar function as the bump 114 in FIGS. 1A and 1B. When the solder block 250a melts, the conductive cylinder 240 and the junction pad 122 are joined together. Hence, the cylindrical bonding structure 260 not only serves as a medium for connecting the chip 110 and the substrate 120 together electrically, the conductive cylinder 240 also serves as an cushioning pad from the chip 110 that pushes the solder block further towards the substrate 120. Note that outer diameter of the conductive cylinder 240 is fixed even when height of the conductive cylinder 240 is increased. Hence, distance of separation between neighboring cylindrical bonding structures 260 and hence neighboring bonding pads 114 (or bonding pads 216) on the chip 110 is shortened.

[0035] According to the first embodiment, the steps involved in fabricating the cylindrical bonding structure include forming a ball contact metallic layer globally over a wafer and then forming a patterned mask layer over the ball contact metallic layer. The mask layer has an opening that surrounds a bonding pad and exposes a portion of the ball contact metallic layer. An electroplating operation is conducted to partially fill the mask opening with conductive material, thereby forming a conductive cylinder. Another electroplating operation or printing operation is conducted to fill up the remaining space of the opening, thereby forming a cylindrical solder cap on the upper surface of the conductive cylinder. Finally, the mask layer and the ball contact metallic layer outside the conductive cylinder are removed to form the cylindrical bonding structure. Furthermore, a reflow operation may also be conducted to transform the cylindrical solder cap into a solder block having a hemispherical shape attached to the upper surface of the conductive cylinder.

[0036] In summary, the method of fabricating the cylindrical bonding structure according to the first embodiment of this invention mainly involves forming a conductive cylinder over the bonding pad of a chip. The conductive cylinder serves as a conductive medium as well as a pad for cushioning up the distance between the chip and the substrate. In addition, by attaching a solder block on the upper end of the conductive cylinder, the conductive cylinder and the junction pad on the substrate are bonded together after the solder block material is partially melted in a reflow operation. Hence, at the same height level, the conductive cylinder can be designed to have an outer diameter smaller than the outer diameter of a spherical bump in a conventional design. Ultimately, the distance of separation between neighboring cylindrical bonding structures and hence the corresponding distance of separation between neighboring bonding pads on the chip can be reduced.

[0037] FIGS. 3A~3E are schematic cross-sectional views showing the progression of steps for producing a cylindrical bonding structure according to a second embodiment of this invention. The second embodiment differs from the first embodiment in that a solder ball is planted onto the upper surface of the conductive cylinder instead of forming the solder block (or the cylindrical solder cap). Since the initial steps as shown in FIGS. 3A~3C for forming the cylindrical bonding structure are identical to the ones shown in FIGS. 2A~2C, detailed description is omitted.

[0038] As shown in FIG. 3D, the mask layer 330 and the ball contact metallic layer 320 outside the conductive cylinder 340 are removed to expose the conductive cylinder 340. As shown in FIG. 3E, a ball placement operation is conducted to attach a solder ball 350 on the upper surface of the conductive cylinder 340. The solder ball 350 serves an identical function as the solder block 250a (or cylindrical solder cap 250) in the first embodiment. Hence, a cylindrical bonding structure 360 is formed on the bonding pad 314 of the chip 316.

[0039] In summary, one major aspect of both the first and the second embodiment of this invention is to form a block of solder material on top of a conductive cylinder for joining the conductive cylinder with junction pad on the substrate. The block of solder material may be shaped into a variety of forms including cylindrical, spherical or hemispherical. The

solder block is formed over the conductive cylinder by depositing solder material into the same opening for forming the conductive cylinder through conducting an electroplating operation or printing operation as in the first embodiment. Alternatively, a solder ball is planted on top of the conductive cylinder as in the second embodiment.

[0040] FIGS. 4A~4F are schematic cross-sectional views showing the progression of steps for producing a cylindrical bonding structure according to a third embodiment of this invention. One major aspect in the third embodiment that differs from the first and the second embodiment of this invention is the control of outer diameter and length of the solder block (or cylindrical solder cap) so that pitch between neighboring bonding pads on a chip can be further reduced.

[0041] As shown in FIG. 4A, a wafer 410 having an active surface 412 is provided. The active surface 412 has a plurality of bonding pads 416 thereon. A passivation layer covers the active surface 412 but exposes the bonding pads 416. A ball contact metallic layer 420 is formed over the entire active surface 412 (the passivation layer 414) of the wafer 410 including the bonding pads 416 by conducting an electroplating operation, evaporation plating operation or sputtering, for example.

[0042] As shown in FIG. 4B, a first patterned mask layer 430 is formed over the ball contact metallic layer 420. The first mask layer 430 has a plurality of openings 432 that corresponds in position to the bonding pads 416 and exposes a portion of the ball contact metallic layer 420. Since the patterned first mask layer 430 is formed in a manner similar to the mask layer 230 in the first embodiment, description is not repeated here.

[0043] As shown in FIG. 4C, an electroplating operation is conducted to deposit conductive material into the openings 432 using the ball contact metallic layer 420 as a seed layer. Hence, conductive cylinders 440 are formed over the ball contact metallic layer 420. Note that the conductive material is a high melting point metal or alloy.

[0044] As shown in FIG. 4D, a second patterned mask layer 434 is formed over the first mask layer 430. The second mask layer 434 has a plurality of openings 436 and exposes the central region of the conductive cylinder 440. Since the patterned second mask layer 434 is formed in a manner similar to the mask layer 230 in the first embodiment, description is not repeated here.

[0045] As shown in FIG. 4E, another electroplating operation is conducted to deposit conductive material into the openings 436 using the conductive cylinder 440 as a seeding layer. Hence, a cylindrical solder cap 450 is formed on the upper surface of each conductive cylinder 440. Note that the conductive material deposited into the openings 436 is a low melting point metal or alloy so that the cylindrical solder cap 450 has a melting point lower than the conductive cylinder 440.

[0046] As shown in FIG. 4F, the first mask layer 430, the second mask layer 434 and the ball contact metallic layer 420 outside the conductive cylinder 440 are removed. The remaining ball contact metallic layer, the conductive cylinder 440 and the cylindrical solder cap 450 together form a cylindrical bonding structure 460.

[0047] FIGS. 5A~5C are schematic cross-sectional views showing an application of the third cylindrical bonding

structure according to this invention to the fabrication of a flip-chip package. As shown in **FIG. 5A**, a cylindrical bonding structure **514** according to the third embodiment of this invention is formed on the bonding pad **512** of a chip **510**. The cylindrical bonding structure **514** comprises a ball contact metallic layer **514a**, a conductive cylinder **514b** and a cylindrical solder cap **514c**. In addition, a substrate **520** having a solder mask layer **524** and a junction pad **522** thereon is also provided. The solder mask **524** has a plurality of openings **526** that exposes the junction pads **522**.

[0048] As shown in **FIG. 5B**, the cylindrical solder cap **514c** has an outer diameter smaller than the diameter of the opening **526** on the solder mask **524**. Hence, tolerance between the cylindrical solder cap **514c** on the cylindrical bonding structure **514** and the junction pad **522** on the substrate **520** is greatly increased. Furthermore, if the conductive cylinder **514b** has an outer diameter greater than the diameter of the opening **526**, the cylindrical solder cap **514c** must be designed to have a length greater than the depth of the opening **526**. Hence, when the cylindrical solder cap **514c** is lowered into the opening **526**, the upper end of the cylindrical solder cap **514c** is able to contact the junction pad **522**.

[0049] As shown in **FIG. 5C**, a reflow process may be conducted after the upper surface of the cylindrical solder cap **514c** is positioned to contact the junction pad **522**. In the reflow process, the cylindrical solder cap **514c** partially melts and joins together the conductive cylinder **514b** and the junction pad **522**. Moreover, an under fill material may be injected into the space between the chip **510** and the substrate **520** to protect the cylindrical bonding structure **514** and serve as a vibration damper.

[0050] The method of fabricating the cylindrical bonding structure according to the third embodiment includes forming a ball contact metallic layer over the surface of a wafer surface and forming a patterned first mask layer over the ball contact metallic layer. The first mask layer has openings that correspond in position to various bonding pads on the wafer and exposes a portion of the ball contact metallic layer. An electroplating operation is conducted to deposit conductive material into the openings of the first mask layer to form conductive cylinders. A patterned second mask layer is formed over the first mask layer. The second mask layer has openings that expose a portion of the upper surface of the conductive cylinders. Similarly, solder material is deposited into the openings of the second mask by conducting an electroplating operation to form cylindrical solder caps over the conductive cylinders. The first mask layer, the second mask layer and the ball contact metallic layer outside the conductive cylinder are removed so that the remaining ball contact metallic layer, the conductive cylinder and the cylindrical solder cap together form a cylindrical bonding structure on the chip.

[0051] One major difference between the cylindrical bonding structure according to the third embodiment and the first two embodiments is that the cylindrical solder cap is designed to have an outer diameter smaller than opening diameter on the solder mask. Hence, the cylindrical solder cap may easily lower into the opening to contact the junction pad on the substrate. This increases the yield of fabricating a flip-chip package and reduces the diameter of the opening. Ultimately, distance of separation between neighboring

junction pads on a substrate and distance of separation between neighboring bonding pads on a chip may both be reduced.

[0052] FIGS. 6A~6E are cross-sectional views showing cylindrical bonding structures fabricated according to this invention with each cylindrical bonding structure having an additional transition layer between the conductive cylinder and the solder cap. As shown in FIGS. 6A~6E, a transition layer **670** is inserted between the conductive cylinder **640** and the solder block **650** in each case. The transition layer **670** may provide different functions according to the constituent materials. Furthermore, the transition layer **670** can be a single layer or a multiple of layers. In **FIG. 6A**, the transition layer **670** provides a function very similar to the ball contact metallic layer **620** between the bonding pad **616** and the conductive cylinder **640**. The transition layer **670** may contain one or a more layers. The transition layer mainly boosts the connectivity between the conductive cylinder **640** and the solder block **650** or prevents the collapse of solder block **650** material onto the peripheral section of the conductive cylinder **640** after conducting a reflow operation leading to a short-circuit between neighboring conductive cylinders.

[0053] The transition layer **670** is fabricated after forming the conductive cylinder **640**. The transition layer **670** is formed over the upper surface of the conductive cylinder **640**. Thereafter, a cylindrical solder cap **650** is formed over the transition layer **670** in **FIG. 6A**, while a solder block having a hemispherical shape is formed over the transition layer **670** in **FIG. 6B**. In **FIG. 6C**, the transition layer **670** is also fabricated on the upper surface of the conductive cylinder **640** after forming the conductive cylinder **640**. However, a solder ball **650** is attached to the transition layer **670** instead of a solder cap. Similarly, in **FIGS. 6D and 6E**, the transition layer **670** is fabricated on the upper surface of the conductive cylinder before forming a solder cap over the transition layer **670**. One major difference is that the transition layer **670** in **FIG. 6D** is formed inside the opening of the patterned first mask layer **430** (in **FIG. 4C**) while the transition layer **670** in **FIG. 6E** is formed inside the opening of the patterned second mask layer **434** (in **FIG. 4D**).

[0054] In conclusion, the cylindrical bonding structure according to this invention is formed by constructing a conductive cylinder over the bonding pad of a chip and using the conductive cylinder to cushion up the distance of separation between the chip and a substrate. The solder block on the tip of the conductive cylinder is also used to join the conductive cylinder to a junction pad on the substrate. Compared with a conventional design using spherical bumps, the cylindrical bonding structure can provide a smaller contact separation. In addition, the solder block may have a variety of profiles including cylindrical, spherical or hemispherical shape. Note that when the solder block has a cylindrical shape, the length and outer diameter of the cylinder may be adjusted to fit into the opening leading to the junction pad. Consequently, outer diameter of the opening may be reduced and separation between neighboring junction pads may be reduced. In other words, separation of neighboring bonding pads on a chip may be reduced.

[0055] Because the conductive cylinder and the junction pad are connected by partially melting the solder block in a reflow process, the step of applying a low melting point

solder material on the junction pads of the substrate or the surface of bumps in a conventional design can be eliminated. Hence, production cost of the flip-chip package is reduced.

[0056] Furthermore, the conventional high-temperature reflow process for shaping the bumps into a spherical shape may result in the formation of excessive oxide material on bump surface and may lead to poor bonding between the bump and the junction pad. In this invention, however, the solder block is formed on the upper surface of the conductive cylinder. A high-temperature reflow process for shaping the solder block into a spherical form is not absolutely required. Even if a spherical shape is demanded, the solder block is shaped using a low-temperature reflow process. Hence, not much oxidation occurs at the surface of the solder block material. Ultimately, a better junction structure is formed linking up the conductive cylinder and the junction pad.

[0057] It will be apparent to those skilled in the art that various modifications and variations can be made to the structure of the present invention without departing from the scope or spirit of the invention. In view of the foregoing, it is intended that the present invention cover modifications and variations of this invention provided they fall within the scope of the following claims and their equivalents.

What is claimed is:

1. A cylindrical bonding structure on a chip having one or more bonding pads thereon, comprising:
 - a conductive cylinder on the bonding pad of the chip; and
 - a solder block on the conductive cylinder, wherein the solder block is made from a material having a melting point lower than the conductive cylinder.
2. The structure of claim 1, wherein the bonding pad is the original bonding pad on the chip.
3. The structure of claim 1, wherein the chip further includes a redistribution circuit layer and the bonding pad is a pad on the redistribution circuit layer.
4. The structure of claim 1, wherein the solder block is a solder ball.
5. The structure of claim 1, wherein the solder block is a cylindrical solder cap.
6. The structure of claim 5, wherein the cylindrical solder cap has an outer diameter smaller than the conductive cylinder.
7. The structure of claim 1, wherein material forming the conductive cylinder is selected from a group consisting of tin, lead, copper, gold, silver, zinc, bismuth, magnesium, antimony, indium and an alloy of the aforementioned metals.
8. The structure of claim 1, wherein material forming the solder block is selected from a group consisting of tin, lead, copper, gold, silver, zinc, bismuth, magnesium, antimony, indium and an alloy of the aforementioned metals.
9. The structure of claim 1, wherein the structure further includes a ball contact metallic layer between the conductive cylinder and the bonding pad.
10. The structure of claim 1, wherein the structure further includes a transition layer between the conductive cylinder and the solder block.
11. The structure of claim 10, wherein the transition layer has at least one conductive layer.

12. A method of forming one or more cylindrical bonding structures over a silicon wafer having an active surface and at least one bonding pad on the active surface, comprising the steps of:
 - forming a ball contact metallic layer over the entire active surface of the silicon wafer, including the bonding pads;
 - forming a patterned mask layer over the ball contact metallic layer, wherein the first mask layer has at least one opening that corresponds in position to the bonding pad and exposes a portion of the ball contact metallic layer;
 - depositing conductive material into the opening to form a conductive cylinder over the ball contact metallic layer, wherein the conductive material only partially fills the opening;
 - depositing solder material into the remaining space of the opening to form at least one cylindrical solder cap on the upper surface of the conductive cylinder, wherein the solder material has a melting point lower than the conductive cylinder material; and
 - removing the mask layer and the ball contact metallic layer outside the conductive cylinder such that the remaining ball contact metallic layer, the conductive cylinder and the cylindrical solder cap together form the cylindrical bonding structure.
13. The method of claim 12, wherein the bonding pad is an original bonding pad on the wafer.
14. The method of claim 12, wherein the wafer further includes a redistribution circuit layer and the bonding pad is a pad on the redistribution circuit layer.
15. The method of claim 12, wherein after removing the mask layer and a portion of the ball contact metallic layer, further includes conducting a reflow operation to transform the cylindrical solder cap into a solder block.
16. The method of claim 12, wherein the step of depositing conductive material into the opening includes conducting an electroplating operation.
17. The method of claim 12, wherein the step of depositing solder material into the opening includes conducting an electroplating or a printing operation.
18. The method of claim 12, wherein after forming the conductive cylinder but before forming the cylindrical solder cap, further includes forming a transition layer over the upper surface of the conductive cylinder so that the cylindrical solder cap is formed over the transition layer.
19. The method of claim 18, wherein the transition layer has at least one conductive layer.
20. The method of claim 12, wherein material forming the conductive cylinder is selected from a group consisting of tin, lead, copper, gold, silver, zinc, bismuth, magnesium, antimony, indium and an alloy of the aforementioned metals.
21. The method of claim 12, wherein material forming the solder block is selected from a group consisting of tin, lead, copper, gold, silver, zinc, bismuth, magnesium, antimony, indium and an alloy of the aforementioned metals.
22. The method of claim 12, wherein material forming the mask layer includes photoresist.
23. The method of claim 12, wherein the step of forming the patterned mask layer includes forming a photoresist layer over the ball contact metallic layer and patterning the photoresist layer.

24. The method of claim 23, wherein the step of patterning the photoresist layer includes conducting a photo-exposure and developing the exposed photoresist layer.

25. A method of forming one or more cylindrical bonding structures over a silicon wafer having an active surface and at least one bonding pad on the active surface, comprising the steps of:

forming a ball contact metallic layer over the entire active surface of the silicon wafer, including the bonding pads;

forming a patterned mask layer over the ball contact metallic layer, wherein the mask layer has at least one opening that corresponds in position to the bonding pad and exposes a portion of the ball contact metallic layer;

depositing conductive material into the opening to form a conductive cylinder over the ball contact metallic layer, wherein the conductive material only partially fills the opening;

removing the mask layer and the ball contact metallic layer outside the conductive cylinder; and

attaching a solder ball onto the upper surface of the conductive cylinder such that the remaining ball contact metallic layer, the conductive cylinder and the solder ball together form the cylindrical bonding structure.

26. The method of claim 25, wherein the bonding pad is the original bonding pad on the wafer.

27. The method of claim 25, wherein the wafer further has a redistribution circuit layer and the bonding pads are pads on the redistribution circuit layer.

28. The method of claim 25, wherein the step of depositing conductive material into the opening includes conducting an electroplating operation.

29. The method of claim 25, wherein after forming the conductive cylinder but before attaching the solder ball, further includes forming a transition layer on the upper surface of the conductive cylinder so that the solder ball is attached to the transition layer.

30. The method of claim 29, wherein the transition layer has at least one conductive layer.

31. The method of claim 25, wherein material forming the conductive cylinder is selected from a group consisting of tin, lead, copper, gold, silver, zinc, bismuth, magnesium, antimony, indium and an alloy of the aforementioned metals.

32. The method of claim 25, wherein material forming the solder ball is selected from a group consisting of tin, lead, copper, gold, silver, zinc, bismuth, magnesium, antimony, indium and an alloy of the aforementioned metals.

33. The method of claim 25, wherein material forming the mask layer includes photoresist.

34. The method of claim 25, wherein the step of forming the patterned mask layer includes forming a photoresist layer over the ball contact metallic layer and patterning the photoresist layer.

35. The method of claim 34, wherein the step of patterning the photoresist layer includes conducting a photo-exposure and developing the exposed photoresist layer.

36. A cylindrical bonding structure on a silicon chip such that the structure may flip over and connect with a substrate, wherein the chip has at least one bonding pad and the substrate has a substrate surface having a patterned solder mask and at least one junction pad thereon, and the solder

mask layer has at least an opening that exposes the junction pad, the cylindrical bonding structure comprising:

a conductive cylinder on the bonding pad of the chip; and
a cylindrical solder cap on the conductive cylinder, wherein the cylindrical solder cap has an outer diameter smaller than the diameter of the opening in the solder mask and a length greater than the depth of the opening, and the solder material has a melting point lower than the conductive cylinder material.

37. The structure of claim 36, wherein the bonding pad is the original bonding pad on the chip.

38. The structure of claim 36, wherein the chip further includes a redistribution circuit layer and the bonding pad is a pad on the redistribution circuit layer.

39. The structure of claim 36, wherein material forming the conductive cylinder is selected from a group consisting of tin, lead, copper, gold, silver, zinc, bismuth, magnesium, antimony, indium and an alloy of the aforementioned metals.

40. The structure of claim 36, wherein material forming the cylindrical solder cap is selected from a group consisting of tin, lead, copper, gold, silver, zinc, bismuth, magnesium, antimony, indium and an alloy of the aforementioned metals.

41. The structure of claim 36, wherein the structure further includes a ball contact metallic layer between the conductive cylinder and the bonding pad.

42. The structure of claim 36, wherein the structure further includes a transition layer between the conductive cylinder and the cylindrical solder cap.

43. The structure of claim 42, wherein the transition layer has at least one conductive layer.

44. A method of forming one or more cylindrical bonding structures over a silicon wafer having an active surface and at least one bonding pad on the active surface, comprising the steps of:

forming a ball contact metallic layer over the entire active surface of the silicon wafer, including the bonding pads;

forming a patterned first mask layer over the ball contact metallic layer, wherein the first mask layer has at least one opening that corresponds in position to the bonding pad and exposes a portion of the ball contact metallic layer;

depositing conductive material into the opening to form a conductive cylinder over the ball contact metallic layer;

forming a patterned second mask layer over the first mask layer, wherein the second mask layer has at least one opening that exposes a portion of the conductive cylinder;

depositing solder material into the opening to form a cylindrical solder cap over the conductive cylinder, wherein the solder material has a melting point lower than the conductive cylinder material; and

removing the first mask layer, the second mask layer and the ball contact metallic layer outside the conductive cylinder such that the remaining ball contact metallic layer, the conductive cylinder and the cylindrical solder cap together form the cylindrical bonding structure.

45. The method of claim 44, wherein the bonding pad is the original bonding pad on the wafer.

46. The method of claim 44, wherein the wafer further has a redistribution circuit layer and the bonding pads are pads on the redistribution circuit layer.

47. The method of claim 44, wherein the step of depositing conductive material into the first mask layer opening includes conducting an electroplating operation.

48. The method of claim 44, wherein the step of depositing solder material into the second mask layer opening includes conducting an electroplating operation.

49. The method of claim 44, wherein after forming the conductive cylinder but before the cylindrical solder cap, further includes forming a transition layer on the upper surface of the conductive cylinder so that the cylindrical solder cap is formed over the transition layer.

50. The method of claim 49, wherein the transition layer has at least one conductive layer.

51. The method of claim 44, wherein material forming the conductive cylinder is selected from a group consisting of tin, lead, copper, gold, silver, zinc, bismuth, magnesium, antimony, indium and an alloy of the aforementioned metals.

52. The method of claim 44, wherein material forming the solder material is selected from a group consisting of tin, lead, copper, gold, silver, zinc, bismuth, magnesium, antimony, indium and an alloy of the aforementioned metals.

53. The method of claim 44, wherein material forming the first mask layer includes photoresist.

54. The method of claim 44, wherein the step of forming the patterned first mask layer includes forming a photoresist layer over the ball contact metallic layer and patterning the photoresist layer.

55. The method of claim 54, wherein the step of patterning the photoresist layer includes conducting a photo-exposure and developing the exposed photoresist layer.

56. The method of claim 44, wherein material forming the second mask layer includes photoresist.

57. The method of claim 44, wherein the step of forming the patterned second mask layer includes forming a photoresist layer over the first mask layer and patterning the photoresist layer.

58. The method of claim 57, wherein the step of patterning the photoresist layer includes conducting a photo-exposure and developing the exposed photoresist layer.

59. A method of connecting a chip to a substrate to form a flip-chip package, wherein the chip has an active surface having at least a bonding pad thereon, the substrate has a substrate surface having a patterned solder mask and at least one junction pad thereon, and the solder mask has at least one opening that exposes the junction pad, the method comprising the steps of:

forming a cylindrical bonding structure on the bonding pad of the chip, wherein the cylindrical bonding structure comprises a conductive cylinder and a solder block, the bottom surface of the conductive cylinder is on top of the bonding pad and the bottom surface of the solder block is on the upper surface of the conductive cylinder, and the solder block has a melting point lower than the conductive cylinder;

flipping over the active surface of the chip to face the substrate surface of the substrate such that the upper surface of the solder block contacts the junction pad; and

conducting a reflow process to melt the solder block material so that the conductive cylinder and the junction pad are joined together.

60. The method of claim 59, wherein the bonding pad is the original bonding pad on the chip.

61. The method of claim 59, wherein the wafer further has a redistribution circuit layer and the bonding pads are pads on the redistribution circuit layer.

62. The method of claim 59, wherein material forming the conductive cylinder is selected from a group consisting of tin, lead, copper, gold, silver, zinc, bismuth, magnesium, antimony, indium and an alloy of the aforementioned metals.

63. The method of claim 59, wherein material forming the solder block is selected from a group consisting of tin, lead, copper, gold, silver, zinc, bismuth, magnesium, antimony, indium and an alloy of the aforementioned metals.

64. The method of claim 59, wherein the solder block is a cylindrical solder cap.

65. The method of claim 64, wherein the cylindrical solder cap has an outer diameter smaller than the opening diameter on the solder mask.

66. The method of claim 65, wherein the cylindrical solder cap has a length greater than the depth of the opening on the solder mask.

67. The method of claim 59, wherein the cylindrical bonding structure further includes a ball contact metallic layer between the conductive cylinder and the bonding pad on the chip.

68. The method of claim 59, wherein the cylindrical bonding structure further includes a transition layer between the conductive cylinder and the solder block.

69. The method of claim 68, wherein the transition layer has at least one conductive layer.

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